Brian Bennett

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/3562519/publications.pdf

Version: 2024-02-01

223 papers	9,493 citations	81900 39 h-index	43889 91 g-index
228 all docs	228 docs citations	228 times ranked	6002 citing authors

#	Article	IF	Citations
1	Electrooptical effects in silicon. IEEE Journal of Quantum Electronics, 1987, 23, 123-129.	1.9	2,166
2	Carrier-induced change in refractive index of InP, GaAs and InGaAsP. IEEE Journal of Quantum Electronics, 1990, 26, 113-122.	1.9	848
3	Robust electrical spin injection into a semiconductor heterostructure. Physical Review B, 2000, 62, 8180-8183.	3.2	466
4	Observation of Spin Injection at a Ferromagnet-Semiconductor Interface. Physical Review Letters, 1999, 83, 203-206.	7.8	445
5	Antimonide-based compound semiconductors for electronic devices: A review. Solid-State Electronics, 2005, 49, 1875-1895.	1.4	319
6	Hybrid Hall effect device. Applied Physics Letters, 1997, 71, 974-976.	3.3	186
7	Evidence of a Hybridization Gap in ``Semimetallic'' InAs/GaSb Systems. Physical Review Letters, 1997, 78, 4613-4616.	7.8	158
8	Photoluminescence studies of selfâ€assembled InSb, GaSb, and AlSb quantum dot heterostructures. Applied Physics Letters, 1996, 68, 3614-3616.	3.3	148
9	Surface reconstruction phase diagrams for InAs, AlSb, and GaSb. Journal of Crystal Growth, 2000, 220, 384-392.	1.5	131
10	Molecular beam epitaxial growth of InSb, GaSb, and AlSb nanometerâ€scale dots on GaAs. Applied Physics Letters, 1996, 68, 505-507.	3.3	129
11	Auger coefficients in type-II InAs/Ga1â^'xInxSb quantum wells. Applied Physics Letters, 1998, 73, 2857-2859.	3.3	128
12	Kramers-Kronig Analysis Of Electro-Optical Switching In Silicon. Proceedings of SPIE, 1987, 0704, 32.	0.8	126
13	AlSb/InAs HEMT's for low-voltage, high-speed applications. IEEE Transactions on Electron Devices, 1998, 45, 1869-1875.	3.0	124
14	Fermi level unpinning of GaSb (100) using plasma enhanced atomic layer deposition of Al2O3. Applied Physics Letters, 2010, 97, 143502.	3.3	97
15	Mobility enhancement in strained p-InGaSb quantum wells. Applied Physics Letters, 2007, 91, .	3.3	93
16	Nanostructure patterns written in IIIâ€“V semiconductors by an atomic force microscope. Applied Physics Letters, 1997, 70, 1855-1857.	3.3	92
17	Optimization of the $hbox{Al}_{2}hbox{O}_{3}/ hbox{GaSb}$ Interface and a High-Mobility GaSb pMOSFET. IEEE Transactions on Electron Devices, 2011, 58, 3407-3415.	3.0	89
18	Electrorefraction and electroabsorption in InP, GaAs, GaSb, InAs, and InSb. IEEE Journal of Quantum Electronics, 1987, 23, 2159-2166.	1.9	77

#	Article	IF	Citations
19	Metallic III-V (001) Surfaces: Violations of the Electron Counting Model. Physical Review Letters, 1997, 79, 693-696.	7.8	76
20	Above-room-temperature optically pumped midinfrared W lasers. Applied Physics Letters, 1998, 73, 3833-3835.	3.3	76
21	Electrical spin injection across air-exposed epitaxially regrown semiconductor interfaces. Applied Physics Letters, 2000, 77, 3989-3991.	3.3	60
22	Long-Period Magnetotelluric Measurements Near the Central California Coast: A Land-Locked View of the Conductivity Structure Under the Pacific Ocean. Geophysical Journal International, 1988, 95, 181-194.	2.4	57
23	Phonons in selfâ€assembled (In,Ga,Al)Sb quantum dots. Applied Physics Letters, 1996, 68, 958-960.	3.3	56
24	Nucleation and growth of Fe on GaAs(001)-(2Ã—4) studied by scanning tunneling microscopy. Physical Review B, 1996, 53, R10481-R10484.	3.2	56
25	Band anticrossing in GaNxSb1â^'x. Applied Physics Letters, 2006, 89, 111921.	3.3	55
26	Strained GaSb/AlAsSb quantum wells for p-channel field-effect transistors. Journal of Crystal Growth, 2008, 311, 47-53.	1.5	55
27	Control of interface stoichiometry in InAs/GaSb superlattices grown by molecular beam epitaxy. Applied Physics Letters, 1993, 63, 949-951.	3.3	53
28	Hammaret al.Reply:. Physical Review Letters, 2000, 84, 5024-5025.	7.8	52
29	A W-band InAs/AlSb low-noise/low-power amplifier. IEEE Microwave and Wireless Components Letters, 2005, 15, 208-210.	3.2	50
30	Band gap reduction in GaNSb alloys due to the anion mismatch. Applied Physics Letters, 2005, 87, 132101.	3.3	49
31	Effect of an in situ hydrogen plasma pre-treatment on the reduction of GaSb native oxides prior to atomic layer deposition. Applied Surface Science, 2013, 277, 167-175.	6.1	48
32	Growth and characterisation of InAs/InGaSb/InAs/AlSb infrared laser structures. Electronics Letters, 1998, 34, 270.	1.0	45
33	Nanometer scale surface clustering on ZnSe epilayers. Applied Physics Letters, 1998, 72, 1238-1240.	3.3	45
34	Device quality Sb-based compound semiconductor surface: A comparative study of chemical cleaning. Journal of Applied Physics, 2011, 109, .	2.5	45
35	Atomic layer deposition of Al2O3 on GaSb using in situ hydrogen plasma exposure. Applied Physics Letters, 2012, 101, 231601.	3.3	45
36	Periodic Scarred States in Open Quantum Dots as Evidence of Quantum Darwinism. Physical Review Letters, 2010, 104, 176801.	7.8	44

#	Article	IF	Citations
37	Open quantum dotsâ€"probing the quantum to classical transition. Semiconductor Science and Technology, 2011, 26, 043001.	2.0	44
38	Orthorhombic distortion of mismatched In X Ga1â^'X As/InP heterostructures. Journal of Electronic Materials, 1991, 20, 1075-1079.	2.2	41
39	Self-assembled InSb and GaSb quantum dots on GaAs(001). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2195.	1.6	41
40	Evolution of GaSb epitaxy on GaAs(001)â€c(4Ã—4). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 885-889.	2.1	40
41	Epitaxial growth, structure, and composition of Fe films on GaAs(001)-2Ã—4. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 3193.	1.6	40
42	Stranski-Krastanov growth of InSb, GaSb, and AlSb on GaAs: structure of the wetting layers. Journal of Crystal Growth, 1997, 175-176, 888-893.	1.5	40
43	Ohmic contacts in AlSb/InAs high electron mobility transistors for low-voltage operation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1022.	1.6	39
44	Interpreting interfacial structure in cross-sectional STM images of IIIâ€"V semiconductor heterostructures. Surface Science, 2000, 465, 361-371.	1.9	39
45	Very-long wave ternary antimonide superlattice photodiode with 21 Î¼m cutoff. Applied Physics Letters, 2003, 82, 4411-4413.	3.3	39
46	Anion control in molecular beam epitaxy of mixed As/Sb III-V heterostructures. Journal of Applied Physics, 1999, 85, 2157-2161.	2.5	38
47	Effects of surface reconstruction on IIIâ€"V semiconductor interface formation: The role of III/V composition. Applied Physics Letters, 1999, 74, 1704-1706.	3.3	38
48	Effects of As[sub 2] versus As[sub 4] on InAs/GaSb heterostructures: As-for-Sb exchange and film stability. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1626.	1.6	38
49	Optimum growth parameters for type-II infrared lasers. Journal of Applied Physics, 1999, 86, 1796-1799.	2.5	37
50	High mobility p-channel HFETs using strained Sb-based materials. Electronics Letters, 2007, 43, 834.	1.0	37
51	InxGa1-xSb channel p-metal-oxide-semiconductor field effect transistors: Effect of strain and heterostructure design. Journal of Applied Physics, 2011, 110, 014503.	2.5	37
52	Enhancing hole mobility in III-V semiconductors. Journal of Applied Physics, 2012, 111, .	2.5	37
53	Surface morphology of homoepitaxial GaSb films grown on flat and vicinal substrates. Journal of Crystal Growth, 2002, 236, 155-164.	1.5	36
54	Planar vibrational modes in superlattices. Physical Review B, 1993, 48, 17172-17176.	3.2	35

#	Article	IF	Citations
55	0.1 [micro sign]m AlSb/InAs HEMTs with InAs subchannel. Electronics Letters, 1998, 34, 1525.	1.0	35
56	Deep level transient capacitance measurements of GaSb self-assembled quantum dots. Journal of Applied Physics, 2000, 88, 5843-5849.	2.5	35
57	Guided-wave intensity modulators using amplitude-and-phase perturbations. Journal of Lightwave Technology, 1988, 6, 437-444.	4.6	34
58	Modulation doping of InAs/AlSb quantum wells using remote InAs donor layers. Applied Physics Letters, 1998, 72, 1193-1195.	3.3	34
59	The structure of Sb-terminated GaAs(001) surfaces. Surface Science, 1999, 436, L707-L714.	1.9	34
60	Interface control in InAs/AlSb superlattices. Applied Physics Letters, 1994, 65, 598-600.	3.3	32
61	Growth of dilute GaNSb by plasma-assisted MBE. Journal of Crystal Growth, 2005, 278, 188-192.	1.5	31
62	Development of high-k dielectric for antimonides and a sub 350°C III–V pMOSFET outperforming Germanium. , 2010, , .		31
63	Investigation of near interface properties in semiâ€insulating InP substrates with epitaxial grown InGaAs and InAlAs by photoreflectance. Journal of Applied Physics, 1993, 73, 1266-1271.	2.5	30
64	High radiation tolerance of InAsâ•AlSb high-electron-mobility transistors. Applied Physics Letters, 2005, 87, 173501.	3.3	30
65	Materials growth for InAs high electron mobility transistors and circuits. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 688.	1.6	29
66	Antimonide-Based Heterostructure p-Channel MOSFETs With Ni-Alloy Source/Drain. IEEE Electron Device Letters, 2013, 34, 1367-1369.	3.9	29
67	Low Temperature Pyrolytic Deposition of High Quality SiO2. Journal of the Electrochemical Society, 1987, 134, 2517-2521.	2.9	28
68	Sb-Based n- and p-Channel Heterostructure FETs for High-Speed, Low-Power Applications. IEICE Transactions on Electronics, 2008, E91-C, 1050-1057.	0.6	28
69	Observation of electrically resettable negative persistent photoconductivity in InAs/AlSb single quantum wells. Applied Physics Letters, 1996, 69, 1417-1419.	3.3	27
70	A RHEED and STM study of Sb-rich AlSb and GaSb (0 0 1) surface reconstructions. Journal of Crystal Growth, 1997, 175-176, 317-322.	1.5	27
71	Magnetoelectronic latching Boolean gate. Solid-State Electronics, 2000, 44, 1099-1104.	1.4	27
72	Transient response of III-V field-effect transistors to heavy-ion irradiation. IEEE Transactions on Nuclear Science, 2004, 51, 3324-3331.	2.0	26

#	Article	IF	Citations
73	W-structured type-II superlattice-based long- and very long wavelength infrared photodiodes. , 2005, , .		26
74	Growth of InAsSb-channel high electron mobility transistor structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1441.	1.6	26
75	Low-Frequency Noise in AlSb/InAs and Related HEMTs. IEEE Transactions on Electron Devices, 2007, 54, 1193-1202.	3.0	26
76	Hole mobility enhancement in In0.41Ga0.59Sb quantum-well field-effect transistors. Applied Physics Letters, 2011, 98, 053505.	3.3	26
77	Origins of interfacial disorder in GaSb/InAs superlattices. Applied Physics Letters, 1995, 67, 3578-3580.	3.3	25
78	Strain relaxation in InAs/GaSb heterostructures. Applied Physics Letters, 1998, 73, 3736-3738.	3.3	25
79	Characterization of single magnetic particles with InAs quantum-well Hall devices. Applied Physics Letters, 2004, 85, 4693-4695.	3.3	25
80	Low-voltage, high-speed AlSb/InAsSb HEMTs. Electronics Letters, 1999, 35, 847.	1.0	24
81	Observation of spin polarized transport across a ferromagnetâ€“two-dimensional electron gas interface (invited). Journal of Applied Physics, 2000, 87, 4665-4669.	2.5	24
82	Charge-collection characteristics of low-power ultrahigh speed, metamorphic AlSb/InAs high-electron mobility transistors (HEMTs). IEEE Transactions on Nuclear Science, 2000, 47, 2662-2668.	2.0	24
83	InAs/GaSb infrared photovoltaic detector at 77 K. Electronics Letters, 1994, 30, 1710-1711.	1.0	22
84	Interface composition control in InAs/GaSb superlattices. Solid-State Electronics, 1994, 37, 733-737.	1.4	22
85	Mismatched InGaAs/InP and InAlAs/InP heterostructures with high crystalline quality. Journal of Applied Physics, 1993, 73, 3195-3202.	2.5	21
86	Determination of temperature dependence of GaSb absorption edge and its application for transmission thermometry. Journal of Applied Physics, 1999, 85, 6632-6635.	2.5	21
87	Monolithic integration of resonant interband tunneling diodes and high electron mobility transistors in the InAs/GaSb/AlSb material system. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1650.	1.6	21
88	Spontaneous growth of an InAs nanowire lattice in an InAs/GaSb superlattice. Applied Physics Letters, 2002, 81, 4452-4454.	3.3	21
89	Design of a shallow thermally stable ohmic contact to p-type InGaSb. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 633.	1.6	21
90	InAs HEMT narrowband amplifier with ultra-low power dissipation. Electronics Letters, 2006, 42, 688.	1.0	21

#	Article	IF	Citations
91	Enhancement-Mode Antimonide Quantum-Well MOSFETs With High Electron Mobility and Gigahertz Small-Signal Switching Performance. IEEE Electron Device Letters, 2011, 32, 1689-1691.	3.9	21
92	Optical anisotropy in mismatched InGaAs/InP heterostructures. Applied Physics Letters, 1991, 58, 2978-2980.	3.3	20
93	Interfacial disorder in InAs/GaSb superlattices. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 77, 7-30.	0.6	20
94	A Low Power/Low Noise MMIC Amplifier for Phased-Array Applications using InAs/AlSb HEMT. , 2006, , .		20
95	High quality HfO2/p-GaSb(001) metal-oxide-semiconductor capacitors with 0.8â€‰nm equivalent oxide thickness. Applied Physics Letters, 2014, 105, .	3.3	20
96	A composite quantum well fieldâ€effect transistor. Applied Physics Letters, 1996, 69, 85-87.	3.3	19
97	Structure of InAs/AlSb/InAs resonant tunneling diode interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2381.	1.6	19
98	Characterization of AlSb/InAs surfaces and resonant tunneling devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1786.	1.6	19
99	Planar vibrational modes as probes of interface structure. Physical Review B, 1994, 50, 1695-1700.	3.2	18
100	Sb-based HEMTs with InAlSbâˆ•InAs heterojunction. Electronics Letters, 2005, 41, 1088.	1.0	18
101	Experimental Determination of Quantum and Centroid Capacitance in Arsenideâ€“Antimonide Quantum-Well MOSFETs Incorporating Nonparabolicity Effect. IEEE Transactions on Electron Devices, 2011, 58, 1397-1403.	3.0	18
102	Enhanced hole mobility and density in GaSb quantum wells. Solid-State Electronics, 2013, 79, 274-280.	1.4	18
103	Interfacial roughness in InAs/GaSb superlattices. Applied Physics Letters, 1994, 64, 3476-3478.	3.3	17
104	Hybrid ferromagnet-semiconductor nonvolatile gate. IEEE Transactions on Magnetics, 1998, 34, 1054-1059.	2.1	17
105	Compound Semiconductors for Low-Power p-Channel Field-Effect Transistors. MRS Bulletin, 2009, 34, 530-536.	3.5	17
106	Lowâ€temperature chemical vapor deposition of SiO2at 2â€“10 Torr. Applied Physics Letters, 1987, 50, 197-199.	3.3	16
107	Transport properties of Be- and Si-doped AlSb. Journal of Applied Physics, 2000, 87, 7876-7879.	2.5	16
108	Low-frequency noise in AlSbâˆ•InAs high-electron-mobility transistor structure as a function of temperature and illumination. Applied Physics Letters, 2004, 85, 774-776.	3.3	16

#	Article	IF	Citations
109	Demonstration of high-mobility electron and hole transport in a single InGaSb well for complementary circuits. Journal of Crystal Growth, 2009, 312, 37-40.	1.5	16
110	Composition and strain of self-assembled (In,Ga,Al)Sb/(Ga,Al)As quantum dots. Superlattices and Microstructures, 1997, 21, 267-272.	3.1	15
111	Photoluminescence of InAs1â^'xSbx/AlSb single quantum wells: Transition from type-II to type-I band alignment. Journal of Applied Physics, 2000, 87, 8192-8194.	2.5	15
112	InAlSb/InAs/AlGaSb Quantum Well Heterostructures for High-Electron-Mobility Transistors. Journal of Electronic Materials, 2007, 36, 99-104.	2.2	15
113	Arsenic cross-contamination in GaSb/InAs superlattices. Journal of Crystal Growth, 2004, 270, 301-308.	1.5	14
114	Strained InGaAs/InAlAs quantum wells for complementary IIIâ€“V transistors. Journal of Crystal Growth, 2014, 388, 92-97.	1.5	14
115	Ultralow Resistance Ohmic Contacts for p-Channel InGaSb Field-Effect Transistors. IEEE Electron Device Letters, 2015, 36, 546-548.	3.9	14
116	Thermal stability of strained InxGa1â^'xAs/InyAl1â^'yAs/InP heterostructures. Applied Physics Letters, 1993, 63, 1122-1124.	3.3	13
117	Optimal epilayer thickness for InxGa1â^'xAs and InyAl1â^'yAs composition measurement by highâ€resolution xâ€ray diffraction. Journal of Applied Physics, 1993, 73, 8304-8308.	2.5	13
118	Engineered heterostructures of 6.1-Angstrom III-V semiconductors for advanced electronic and optoelectronic applications. , 1999, 3790, 13.		13
119	Barrier roughness effects in resonant interband tunnel diodes. Journal of Applied Physics, 2001, 90, 6177-6181.	2.5	13
120	Lateral composition modulation in InAs/GaSb superlattices. Journal of Applied Physics, 2003, 93, 311-315.	2.5	13
121	Low-frequency noise characteristics of AlSb/InAsSb HEMTs. Solid-State Electronics, 2004, 48, 2079-2084.	1.4	13
122	Engineering of strained III–V heterostructures for high hole mobility. , 2009, , .		13
123	Influence of interace and buffer layer on the structure of InAs/GaSb superlattices. Applied Physics Letters, 1995, 67, 1609-1611.	3.3	12
124	A tunneling field-effect transistor with 25 nm metallurgical channel length. Applied Physics Letters, 1997, 70, 3005-3007.	3.3	12
125	AlSb/InAs HEMTs using modulation InAs(Si)-doping. Electronics Letters, 1998, 34, 403.	1.0	12
126	Strong emission from As monolayers in AlSb. Physical Review B, 1999, 59, 2240-2244.	3.2	12

#	Article	IF	Citations
127	Low-frequency noise in AlSb/InAs HEMTs. Electronics Letters, 2000, 36, 1888.	1.0	12
128	Controlled n-type doping of antimonides and arsenides using GaTe. Journal of Crystal Growth, 2003, 251, 532-537.	1.5	12
129	Manufacturable and Reliable 0.1 μm AlSb/InAs HEMT MMIC Technology for Ultra-Low Power Applications. , 2007, , .		12
130	Effect of Interface States on the Performance of Antimonide nMOSFETs. IEEE Electron Device Letters, 2013, 34, 360-362.	3.9	12
131	Enhancing p-channel InGaSb QW-FETs via Process-Induced Compressive Uniaxial Strain. IEEE Electron Device Letters, 2014, 35, 1088-1090.	3.9	12
132	Magnetocapacitance and far-infrared photoconductivity in GaSb/InAs composite quantum wells. Physical Review B, 1999, 60, R13958-R13961.	3.2	11
133	A 110-GHz AlSb/InAs MMIC amplifier. , 0, , .		11
134	InAlAsSbâˆ•InGaSb double heterojunction bipolar transistor. Electronics Letters, 2005, 41, 370.	1.0	11
135	Sulfur passivation for shallow Pdâˆ•Wâˆ•Au ohmic contacts to p-InGaSb. Applied Physics Letters, 2004, 85, 3471-3473.	3.3	10
136	InAsâˆ•AlSb high-electron-mobility transistors by molecular-beam epitaxy for low-power applications. Journal of Vacuum Science & Technology B, 2006, 24, 2581.	1.3	10
137	Scaling projections for Sb-based p-channel FETs. Solid-State Electronics, 2010, 54, 1349-1358.	1.4	10
138	InGaSb: Single channel solution for realizing III–V CMOS. , 2012, , .		10
139	Mapping of the localized interface and surface states of InGaAs lattice matched to Feâ€doped InP by infrared spectroscopy. Journal of Applied Physics, 1992, 72, 3664-3669.	2.5	9
140	Origin of optical anisotropy in strained InxGa1âˆ’xAs/InP and InyAl1âˆ’yAs/InP heterostructures. Journal of Electronic Materials, 1994, 23, 423-429.	2.2	9
141	AlSb/InAs HEMTs with high transconductance and negligible kink effect. Electronics Letters, 1996, 32, 688.	1.0	9
142	Microwave noise characteristics of AlSb/InAs HEMTs. Electronics Letters, 1997, 33, 1092.	1.0	9
143	Proton irradiation of InAs/AlSb/GaSb resonant interband tunneling diodes. Applied Physics Letters, 2001, 78, 2581-2583.	3.3	9
144	Resonant interband tunnel diodes with AlGaSb barriers. Journal of Applied Physics, 2001, 89, 5791-5793.	2.5	9

#	Article	IF	Citations
145	Amelioration of interface state response using band engineering in III-V quantum well metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2012, 100, .	3.3	9
146	Structural and Electrical Properties of Lowâ€Temperature, Lowâ€Pressure SiO2 on Si. Journal of the Electrochemical Society, 1992, 139, 1684-1690.	2.9	8
147	Surface photovoltage spectroscopy of InxAl1âˆ’xAs epilayers. Journal of Applied Physics, 1995, 78, 7163-7169.	2.5	8
148	Charge-collection dynamics of AlSb-InAs-GaSb resonant interband tunneling diodes (RITDs) [for MOBILE logic circuits]. IEEE Transactions on Nuclear Science, 2001, 48, 1973-1979.	2.0	8
149	Stoichiometry-induced roughness on antimonide growth surfaces. Applied Physics Letters, 2001, 78, 2440-2442.	3.3	8
150	AlSb/InAs HEMTs with a TiW/Au gate metalization for improved stability. Solid-State Electronics, 2003, 47, 181-184.	1.4	8
151	Shallow and thermally stable Ptâˆ•Wâˆ•Au Ohmic contacts to p-type InGaSb. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 293-297.	2.1	8
152	Growth of dilute nitride alloys of GaInSb lattice-matched to GaSb. Journal of Crystal Growth, 2007, 304, 338-341.	1.5	8
153	Imaging scarred states in quantum dots. Journal of Physics Condensed Matter, 2009, 21, 212201.	1.8	8
154	Morphological instability in InAs/GaSb heterostructures. Journal of Crystal Growth, 1998, 191, 651-662.	1.5	7
155	Molecular Beam Epitaxy of Sb-based Semiconductors. Series on Directions in Condensed Matter Physics, 1999, , 401-452.	0.1	7
156	Antimonide-based diodes for terahertz mixers. Applied Physics Letters, 2008, 92, .	3.3	7
157	AlGaSb Buffer Layers for Sb-Based Transistors. Journal of Electronic Materials, 2010, 39, 2196-2202.	2.2	7
158	Advanced composite high-κ gate stack for mixed anion arsenide-antimonide quantum well transistors. , 2010, , .		7
159	Characterization of surface roughness anisotropy on mismatched InAlAs/InP heterostructures. Journal of Electronic Materials, 1996, 25, 313-319.	2.2	6
160	Initial stages of Sb2 deposition on InAs(001). Surface Science, 2001, 478, 1-8.	1.9	6
161	Suppression of Bulk Defects in Antimonide Superlattice Infrared Photodiodes. Materials Research Society Symposia Proceedings, 2002, 722, 1011.	0.1	6
162	Characterization of InGaSb by photoreflectance spectroscopy. Journal of Applied Physics, 2002, 91, 1175-1178.	2.5	6

#	Article	IF	Citations
163	Pd/Pt/Au ohmic contact for AlSb/InAs0.7Sb0.3 heterostructures. Solid-State Electronics, 2006, 50, 429-432.	1.4	6
164	Reliability Evaluation of 0.1 Â¿m AlSb/InAs HEMT Low Noise Amplifiers for Ultralow-Power Applications. , 2007, , .		6
165	Electronic properties of atomic-layer-deposited high-k dielectrics on GaSb(001) with hydrogen plasma pretreatment. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 04E102.	1.2	6
166	0.2 Âµm AlSb/InAs HEMTs with 5 V gate breakdown voltage. Electronics Letters, 1994, 30, 1983-1984.	1.0	5
167	Growth of the (In,Al,Ga)As quaternary alloy system on GaAs at low substrate temperatures by molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 1099.	1.6	5
168	Charge trapping and built-in field studies in electroreflectance of a GaAs structure. Semiconductor Science and Technology, 1996, 11, 521-524.	2.0	5
169	Heterostructure interface effects on the far-infrared magneto-optical spectra of InAs/Gasb quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 186-189.	2.7	5
170	Fermi level unpinning of GaSb(100) using Plasma Enhanced ALD Al<inf>2</inf>O<inf>3</inf> dielectric. , 2010, , .		5
171	Integration of atomic layer deposited high-k dielectrics on GaSb via hydrogen plasma exposure. AIP Advances, 2014, 4, .	1.3	5
172	Electrical properties of low-temperature pyrolytic SiO2 on InP. Electronics Letters, 1988, 24, 172.	1.0	5
173	Properties of low-temperature (80-300Â° C) pyrolytic SiO2 on Si and InP. Journal of Electronic Materials, 1988, 17, 365-371.	2.2	4
174	Heterostructure design and demonstration of InGaSb channel III-V CMOS transistors. , 2011, , .		4
175	Molecular Beam Epitaxial Regrowth of Antimonide-Based Semiconductors. Journal of Electronic Materials, 2011, 40, 6-10.	2.2	4
176	Antimonide NMOSFET with source side injection velocity of 2.7×10⁷ cm/s for low power high performance logic applications. , 2012, , .		4
177	Analysis Of Franz-Keldysh Electro-Optic Modulation In InP, GaAs, GaSb, InAs, And InSb. , 1987, 0836, 158.		3
178	High-Quality InAs/A1Sb Superlattices with AlAs and InSb Interfaces. Materials Research Society Symposia Proceedings, 1994, 340, 253.	0.1	3
179	The effect of gate metals on manufacturability of 0.1 μm metamorphic AlSb/InAs HEMTs for ultralow-power applications. , 2008, , .		3
180	Study of Shubnikovâ€“de Haas oscillations and measurement of hole effective mass in compressively strained InXGa1â^'XSb quantum wells. Solid-State Electronics, 2011, 62, 138-141.	1.4	3

#	Article	IF	Citations
181	Ion-Induced Charge-Collection Transients in p-Channel AlGaSb/InGaSb Heterojunction Field-Effect Transistors. IEEE Transactions on Nuclear Science, 2014, 61, 1510-1515.	2.0	3
182	Single Event Measurement and Analysis of Antimony Based n-Channel Quantum-Well MOSFET With High-<formula formulatype="inline"><tex Notation="TeX">$kappa$</tex> </formula> Dielectric. IEEE Transactions on Nuclear Science, 2015, 62, 2807-2814.	2.0	3
183	Effect of illumination on the interplay between Dresselhaus and Rashba spin-orbit couplings in InAs quantum wells. Journal of Applied Physics, 2019, 126, .	2.5	3
184	Charge scattering mechanisms in shallow InAs quantum wells. Journal of Applied Physics, 2020, 127, .	2.5	3
185	An instrument system for low-frequency (10^{â^'3}â€“10³ Hz) impedance measurements. IEEE Transactions on Instrumentation and Measurement, 1986, IM-35, 287-292.	4.7	2
186	Carrier refraction in quantum well waveguides. Applied Optics, 1989, 28, 3577.	2.1	2
187	Index of Refraction Anisotropy in InGaAs/InP Heterostructures Measured by Ellipsometry. Materials Research Society Symposia Proceedings, 1989, 160, 713.	0.1	2
188	Growth of InP high electron mobility transistor structures with Te doping. Journal of Crystal Growth, 2005, 278, 596-599.	1.5	2
189	Sb-based n- and p-channel HFETs for high-speed, low-power applications. , 2009, , .		2
190	Spatial localization of 1/f noise sources in AlSb/InAs high-electron-mobility transistors. Journal of Applied Physics, 2009, 106, .	2.5	2
191	Experimental determination of dominant scattering mechanisms in scaled InAsSb quantum well. , 2011, , .		2
192	III-Sb MOSFETS : Opportunities and Challenges. ECS Transactions, 2012, 45, 91-96.	0.5	2
193	Effects of oxidant dosing on GaSb (100) prior to atomic layer deposition and high-performance antimonide-based P-channel MOSFETs with Ni-alloy S/D. , 2013, , .		2
194	Step graded buffer for (110) InSb quantum wells grown by molecular beam epitaxy. Journal of Crystal Growth, 2014, 404, 122-129.	1.5	2
195	Microbial Degradation of Diesel Fuel. Transactions of the Kansas Academy of Science, 1982, 85, 72.	0.1	1
196	Bandfilling Electro-Optic Effect In InP, GaAs, GaSb, InAs, and InSb. Proceedings of SPIE, 1989, , .	0.8	1
197	Relaxation of Mismatched In_xAl_{1â^'x}As/InP Heterostructures. Materials Research Society Symposia Proceedings, 1991, 240, 153.	0.1	1
198	Photoreflectance Characterization of the Semi-Insulating InP Substrate Interface with InGaAs and InAlAs Epilayers. Materials Research Society Symposia Proceedings, 1992, 281, 121.	0.1	1

#	Article	IF	Citations
199	Electro-optic Fabryâ€“Perot pixels for phase-dominant spatial light modulators. Applied Optics, 1992, 31, 675.	2.1	1
200	Study of lattice-mismatched (In,Ga)As/GaAs heterostructures on the unconventional (110) GaAs surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 1095.	1.6	1
201	<title>InAs-GaSb-AlSb quantum confined structures for IR applications</title>. , 1995, , .		1
202	Synthetic wide bandpass x-ray polarizers. Applied Physics Letters, 1997, 70, 2224-2226.	3.3	1
203	Optical and magnetic resonance studies of As-impurities in AlSb: from isoelectronic point defects to planes. Physica B: Condensed Matter, 1999, 273-274, 811-814.	2.7	1
204	Controlled n-type doping of antimonide/arsenide heterostructures using GaTe. , 0, , .		1
205	Magnetotunneling between two-dimensional electron gases in InAs-AlSb-GaSb heterostructures. Physical Review B, 2003, 68, .	3.2	1
206	0.1 um n+-InAs-AlSb-InAs HEMT MMIC Technology for Phased-Array Applications. , 2007, , .		1
207	1/f noise of Sb-based p-channel HFETs. Electronics Letters, 2008, 44, 1155.	1.0	1
208	Using Density-Gradient Theory to Model Sb-Based p-Channel FETs. , 2009, , .		1
209	Fermi-level pinning at metal/antimonides interface and demonstration of antimonides-based metal S/D Schottky pMOSFETs. , 2011, , .		1
210	Growth and characterization of (110) InAs quantum well metamorphic heterostructures. Journal of Applied Physics, 2015, 117, .	2.5	1
211	Single event transient response of InGaSb p-MOSFETs using pulsed laser excitation: Comparison of buried-channel and surface-channel structures. , 2016, , .		1
212	Single-Event Measurement and Analysis of Antimony-Based p-Channel Quantum-Well MOSFETs With High- $kappa $ Dielectric. IEEE Transactions on Nuclear Science, 2017, 64, 434-440.	2.0	1
213	MIS Structures On InP Using Oxide Deposited Near 100Â°C. Proceedings of SPIE, 1989, 1144, 233.	0.8	0
214	The Growth of Type-II Infrared Laser Structures. Materials Research Society Symposia Proceedings, 1997, 484, 11.	0.1	0
215	X-ray diffraction analysis of lateral composition modulation in InAs/GaSb superlattices intended for infrared detector applications. IEE Proceedings: Optoelectronics, 2003, 150, 420.	0.8	0
216	High speed, low power electronics using Sb-based semiconductors. , 0, , .		0

#	Article	IF	Citations
217	Modeling gate leakage in InAs/AlSb HEMTs. , 2003, , .		0
218	0.1 μm In₀₂Al₀₈Sb-InAs HEMT low-noise amplifiers for ultralow-power applications. , 2007, , .		0
219	Manufacturable tri-stack AlSb/INAS HEMT low-noise amplifiers using wafer-level-packaging technology for light-weight and ultralow-power applications. , 2009, , .		0
220	Imaging periodic scarred states in InAs open quantum dots: Evidence of quantum darwinism. , 2010, , .		0
221	Ion-induced charge-collection transients in p-channel AlGaSb/InGaSb field-effect transistors. , 2013, , .		0
222	Detection of ferromagnetic domain wall pinning and depinning with a semiconductor device. Journal of Applied Physics, 2015, 118, 234501.	2.5	0
223	Strained InGaSb/AlGa(As)Sb Quantum Wells for p-Channel Transistors. Journal of Electronic Materials, 2016, 45, 2757-2762.	2.2	0